

## Power Amplifier Module for JCDMA

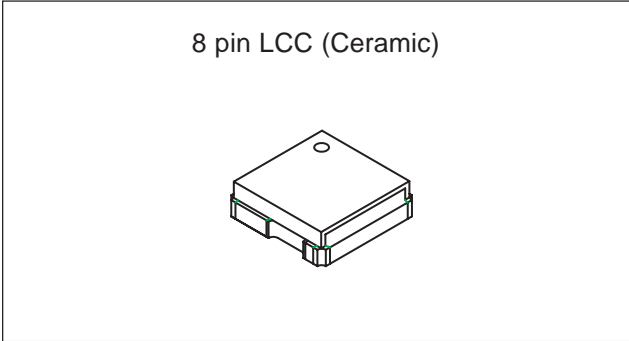
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**Description**

The CXG1178K is the power amplifier module which operates at a single power supply. This IC is designed using the Sony's original p-Gate HFET process.

**Features**

- Single power supply operation:  
 $V_{DD1} = V_{DD2} = 3.5V$  (High mode),  
                                   1.5V (Mid mode),  
                                   1.0V (Low mode),  
 $V_{GG} = 2.8V$
- Ultrasmall package: 0.027cc (4.5mm × 4.5mm × 1.35mm)
- High efficiency:  $\eta_{add} = 40.5\%$  @  $P_{OUT} = 27.5dBm$  (High mode),  
                                    $\eta_{add} = 17.6\%$  @  $P_{OUT} = 14dBm$  (Mid mode)
- Output power (High/Mid/Low mode switching supported):  
 $P_{OUT} = 18$  to 27.5dBm: High mode,  
 $P_{OUT} = 14$  to 18dBm: Mid mode,  
 $P_{OUT} \leq 14dBm$ : Low mode
- Gain (High mode):  $G_p = 28.5dB$  (@900MHz)



**Applications**

Power amplifier for JCDMA system cellular phones

**Structure**

p-Gate HFET module

**Absolute Maximum Ratings** ( $T_a = 25^\circ C$ )

• Operating case temperature	$T_{case}$	-30 to +110	$^\circ C$
• Storage temperature	$T_{stg}$	-30 to +125	$^\circ C$
• Bias voltage	$V_{DD1}, V_{DD2}$	6	V
• Bias voltage	$V_{GG}$	3.3	V
		(@ $V_{DD1} = V_{DD2} \leq 3.5V$ )	
• Input power	$P_{IN}$	8	dBm

**Recommended Bias Voltage Conditions**

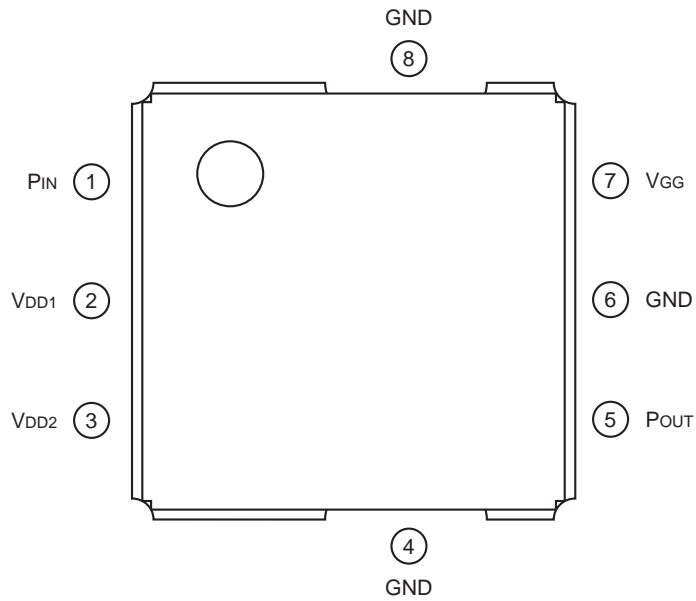
- $V_{DD1} = V_{DD2} = 1.0$  to 4.2V
- $V_{GG} = 2.8V \pm 1\%$

Descriptions in this specification are specified for the Sony's recommended evaluation board . GaAs module is ESD sensitive devices. Special handling precautions are required.

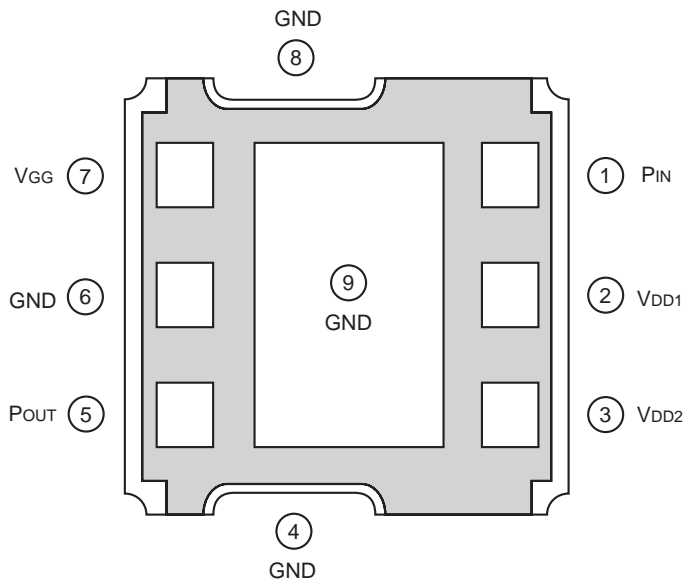
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Package Outline/Pin Configuration

Front



Back



**Note)** Pin 4, 8 and 9 should be soldered on the land of the board.

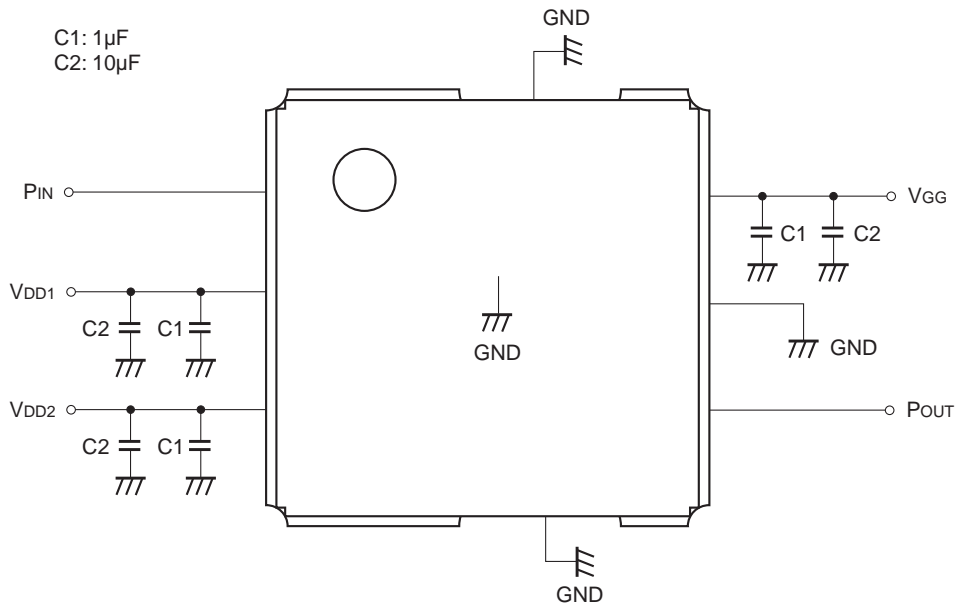
For the land to which Pin 9 is connected, make the through holes in the land and form the GND pattern.

## Electrical Characteristics

(ZS = ZL = 50Ω, IS-95 Modulation, Ta = 25°C)

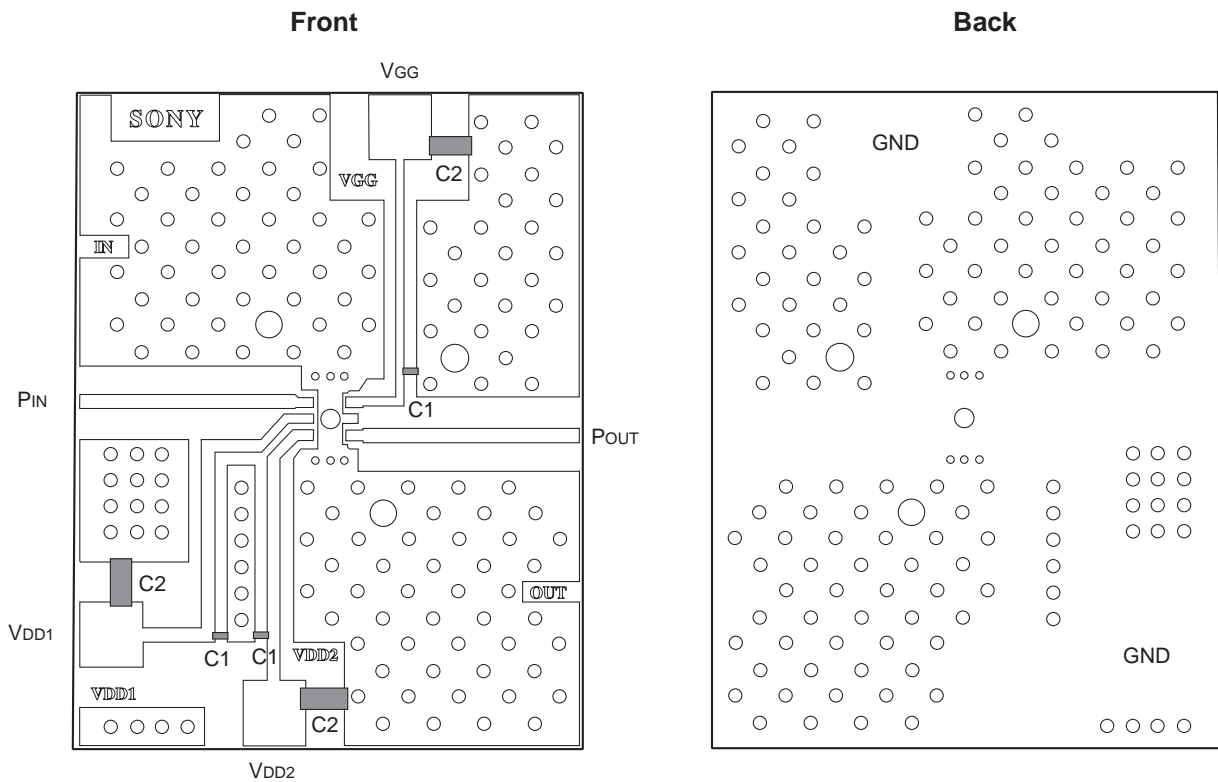
Item	Conditions	Min.	Typ.	Max.	Unit
Frequency		887		925	MHz
Current consumption 1	P <sub>OUT</sub> = 27.5dBm, V <sub>DD1</sub> = V <sub>DD2</sub> = 3.5V, V <sub>GG</sub> = 2.8V		397	412	mA
Current consumption 2	P <sub>OUT</sub> = 14dBm, V <sub>DD1</sub> = V <sub>DD2</sub> = 1.5V, V <sub>GG</sub> = 2.8V		95	102	mA
Current consumption 3	P <sub>OUT</sub> = 9dBm, V <sub>DD1</sub> = V <sub>DD2</sub> = 1.0V, V <sub>GG</sub> = 2.8V		59	66	mA
Gain 1	P <sub>OUT</sub> = 27.5dBm, V <sub>DD1</sub> = V <sub>DD2</sub> = 3.5V, V <sub>GG</sub> = 2.8V	26.5	28.5		dB
Gain 2	P <sub>OUT</sub> = 18dBm, V <sub>DD1</sub> = V <sub>DD2</sub> = 1.5V, V <sub>GG</sub> = 2.8V	20.5	22.5		dB
Gain 3	P <sub>OUT</sub> = 14dBm, V <sub>DD1</sub> = V <sub>DD2</sub> = 1.0V, V <sub>GG</sub> = 2.8V	17.5	19.5		dB
ACPR1 (High mode)	P <sub>OUT</sub> = 27.5dBm, V <sub>DD1</sub> = V <sub>DD2</sub> = 3.5V, V <sub>GG</sub> = 2.8V, ±900kHz offset, 30kHz band width		-52	-47	dBc
ACPR2 (High mode)	P <sub>OUT</sub> = 27.5dBm, V <sub>DD1</sub> = V <sub>DD2</sub> = 3.5V, V <sub>GG</sub> = 2.8V, ±1.98MHz offset, 30kHz band width		-62	-57	dBc
ACPR1 (Mid mode)	P <sub>OUT</sub> = 18dBm, V <sub>DD1</sub> = V <sub>DD2</sub> = 1.5V, V <sub>GG</sub> = 2.8V, ±900kHz offset, 30kHz band width		-55	-47	dBc
ACPR2 (Mid mode)	P <sub>OUT</sub> = 18dBm, V <sub>DD1</sub> = V <sub>DD2</sub> = 1.5V, V <sub>GG</sub> = 2.8V, ±1.98MHz offset, 30kHz band width		-62	-57	dBc
ACPR1 (Low mode)	P <sub>OUT</sub> = 14dBm, V <sub>DD1</sub> = V <sub>DD2</sub> = 1.0V, V <sub>GG</sub> = 2.8V, ±900kHz offset, 30kHz band width		-54	-47	dBc
ACPR2 (Low mode)	P <sub>OUT</sub> = 14dBm, V <sub>DD1</sub> = V <sub>DD2</sub> = 1.0V, V <sub>GG</sub> = 2.8V, ±1.98MHz offset, 30kHz band width		-63	-57	dBc
2nd harmonics	P <sub>OUT</sub> = 27.5dBm, V <sub>DD1</sub> = V <sub>DD2</sub> = 3.5V, V <sub>GG</sub> = 2.8V		-41	-30	dBc
3rd harmonics	P <sub>OUT</sub> = 27.5dBm, V <sub>DD1</sub> = V <sub>DD2</sub> = 3.5V, V <sub>GG</sub> = 2.8V		-57	-30	dBc
Gate current	P <sub>OUT</sub> ≤ 27.5dBm, V <sub>GG</sub> = 2.8V		1.8	2.5	mA
Idle current 1	P <sub>IN</sub> , P <sub>OUT</sub> = None, V <sub>DD1</sub> = V <sub>DD2</sub> = 3.5V, V <sub>GG</sub> = 2.8V		85	110	mA
Idle current 2	P <sub>IN</sub> , P <sub>OUT</sub> = None, V <sub>DD1</sub> = V <sub>DD2</sub> = 1.5V, V <sub>GG</sub> = 2.8V		51	66	mA
Idle current 3	P <sub>IN</sub> , P <sub>OUT</sub> = None, V <sub>DD1</sub> = V <sub>DD2</sub> = 1.0V, V <sub>GG</sub> = 2.8V		40	52	mA

**Recommended External Circuit**



**Recommended Evaluation Board**

Board material: Glass fabric-base epoxy  
 Size: 40mm × 50mm × 0.6mm  
 Relative dielectric constant: 4.6



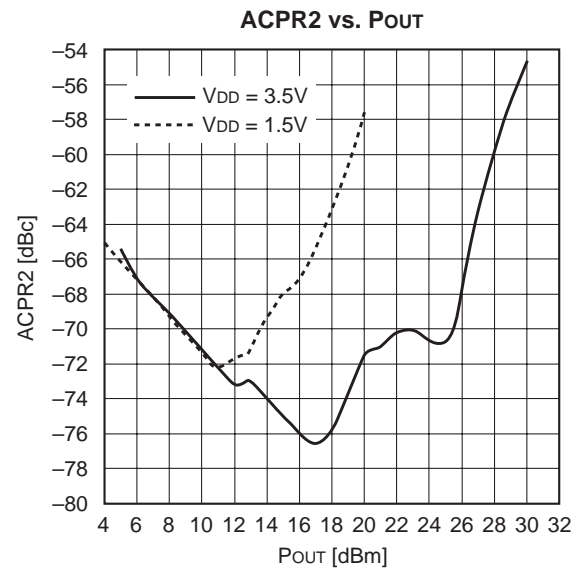
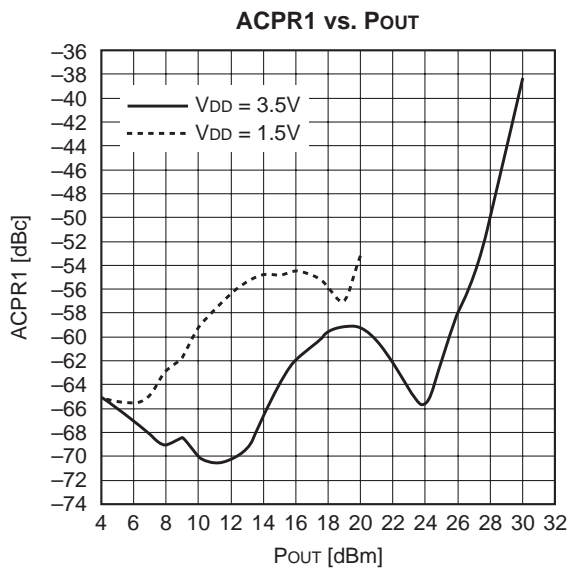
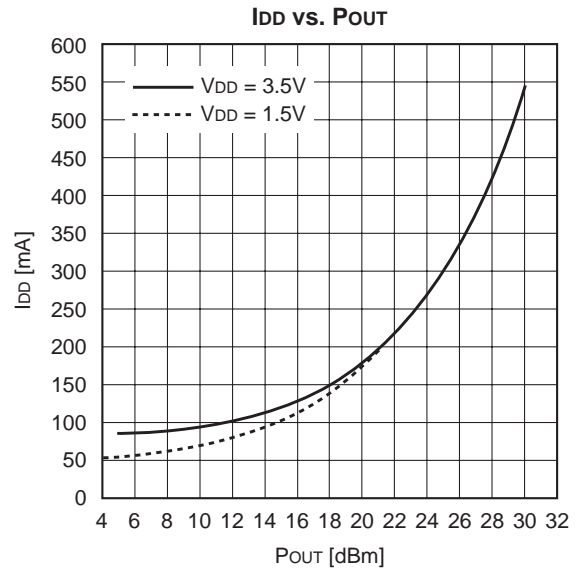
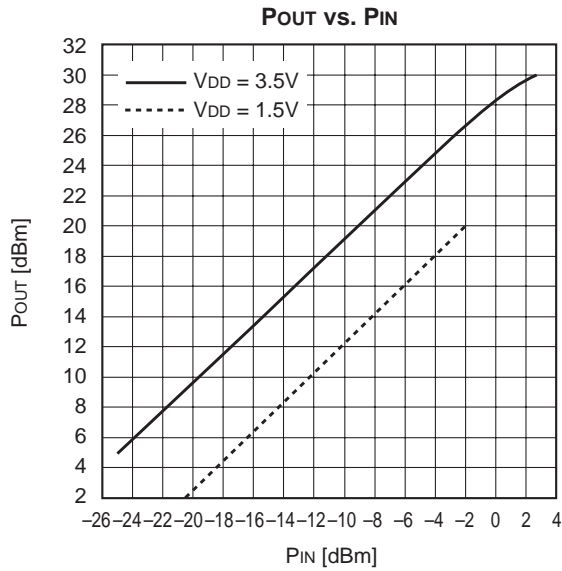
Example of Representative Characteristics

Conditions:  $f = 900\text{MHz}$

$V_{DD1} = V_{DD2} = 3.5\text{V}$ ,  $V_{GG} = 2.8\text{V}$  (High mode)

$V_{DD1} = V_{DD2} = 1.5\text{V}$ ,  $V_{GG} = 2.8\text{V}$  (Mid mode)

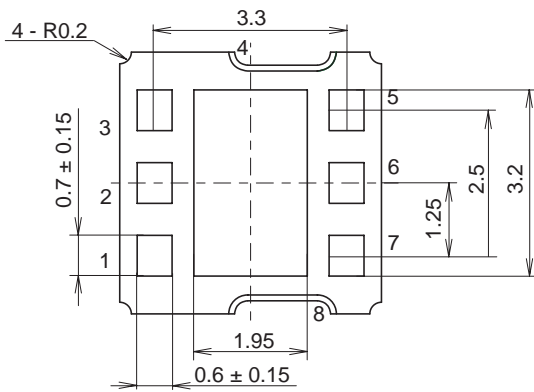
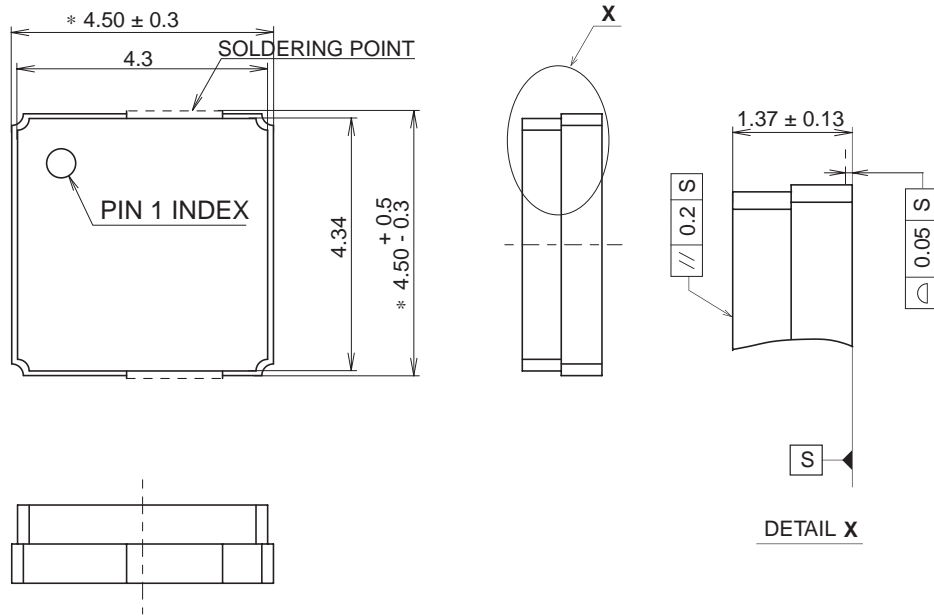
$T_a = 25^\circ\text{C}$



Package Outline

Unit: mm

8PIN LCC



NOTE: Dimension "\*" does not include cutting burr.

SONY CODE	LCC-8C-371
EIAJ CODE	_____
JEDEC CODE	_____

PACKAGE STRUCTURE

PACKAGE MATERIAL	CERAMIC SUBSTRATE
TERMINAL TREATMENT	GOLD PLATING
TERMINAL MATERIAL	NICKEL PLATING
PACKAGE MASS	0.08g